

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method for manufacturing a semiconductor device equipped with a capacitor in which a dielectric film is used, wherein a conductive complex oxide having an exposed top surface is used as a mask material when the dielectric film is subjected to reactive ion etching, and the mask material, which is in direct contact with the dielectric film, is used as an upper electrode of the capacitor after the reactive ion etching is performed, an area of a top surface of the dielectric film being equal to an area of a bottom surface of the mask material after the reactive ion etching.

Claim 2 (Original): The method according to claim 1, wherein the complex oxide contains SrRuO₃ as a main component.

Claims 3-4 (Cancelled).

Claim 5 (Original): The method according to claim 1, wherein the dielectric film contains PZT as a main component.

Claim 6 (Previously Presented): The method according to claim 1, wherein Pt, Ir, Ru, IrO₂, RuO₂, or a laminated structure or a mixture of them is used as a material of a lower electrode of the capacitor.

Claims 7-10 (Cancelled).